

200mA30V(Twin Chip Type)

Chip Information

Chip Size	0.45 x 0.45mm
Pad Size	0.36 x 0.16mm
Chip Quantity	54488 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	4	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.240	0.235	0.220	V	IF=100uA Ta=25degC
	VF2	0.320	0.310	0.285	V	IF=1mA Ta=25degC
	VF3	0.400	0.390	0.355	V	IF=10mA Ta=25degC
	VF4	0.500	0.480	0.410	V	IF=30mA Ta=25degC
	VF5	1.000	0.800	0.535	V	IF=100mA Ta=25degC
Maximum DC Reverse Current	IR1	0.5	0.4	0.009	uA	VR=25V Ta=25degC
	IR2	2	1	0.12	uA	VR=30V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	30	36	55	V	IR=10uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
XFA225	180 +/- 20um	Au (For Eutectic)
XFA227	150 +/- 20um	Au (For Eutectic)
XFA226	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:

Designed For BAT54,BAT42W,BAT43W